### OP593, OP598 Series

#### Features:

- Dark blue epoxy package
- Wide receiving angle
- Variety of sensitivity ranges
- TO-18 equivalent package style

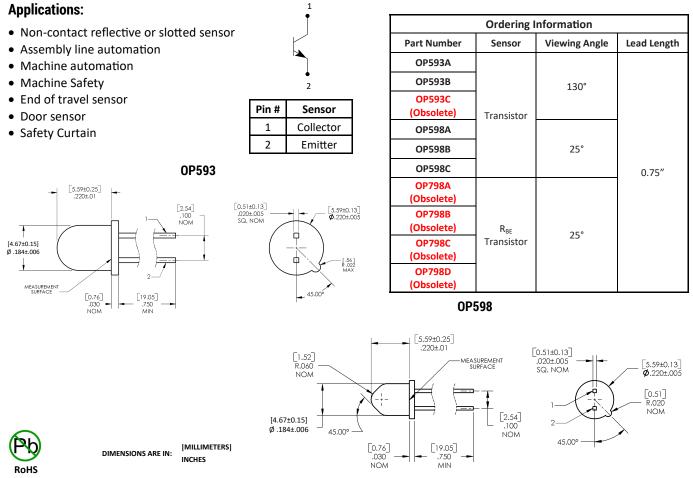


#### **Description:**

Each device in this series consists of an NPN silicon phototransistor molded in a dark blue epoxy packages. The wide receiving angle (130°) of the **OP593** series devices provides relatively even reception over a large area. The narrow receiving angle (25°) of the **OP598** series devices provides a relatively small reception area.

These devices are 100% production tested using infrared light for close correlation with OPTEK's GaAs and GaAIAs emitters.

Please refer to Application Bulletins 208 and 210 for additional design information and reliability (degradation) data.



General Note

TT Electronics reserves the right to make changes in product specification without notice or liability. All information is subject to TT Electronics' own data and is considered accurate at time of going to print.



## OP593, OP598 Series

### **Electrical Specifications**

#### Absolute Maximum Ratings (T<sub>A</sub> = 25° C unless otherwise noted)

Storage and Operating Temperature Range	-40° C to +100° C
Collector-Emitter Voltage	30 V
Emitter-Collector Voltage	5 V
Continuous Collector Current	50 mA
Lead Soldering Temperature [1/16 inch (1.6 mm) from case for 5 seconds with soldering iron]	260° C <sup>(1)</sup>
Power Dissipation	250 mW <sup>(2)</sup>

#### Electrical Characteristics (T<sub>A</sub> = 25° C unless otherwise noted)

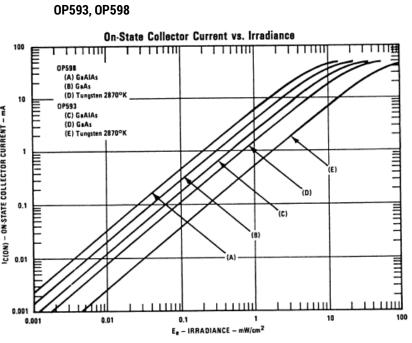
SYMBOL	PARAMETER	MIN	ТҮР	MAX	UNITS	TEST CONDITIONS
I <sub>C(ON)</sub>	On-State Collector Current OP593A OP593B OP598A OP598B OP598C	3.0 2.0 7.5 5.0 2.5	- - - -	4 4 10 10 10	mA	$V_{CE} = 5$ V. Light source is an unfiltered GaAlAs LED with a peak emission wave- length of 890 nm and $E_{e(APT)}$ of 1.7 mW/ cm <sup>2</sup> average within a .250" diameter aperture.
I <sub>CEO</sub>	Collector-Dark Current	-	-	100	nA	$V_{CE} = 10 V, E_{E} = 0$
V <sub>(BR)CEO</sub>	Collector-Emitter Breakdown Voltage	30	-	-	V	I <sub>C</sub> = 100 μA
V <sub>(BR)ECO</sub>	Emitter-Collector Breakdown Voltage	5	-	-	V	I <sub>E</sub> = 100 μA
V <sub>CE(SAT)</sub>	Collector-Emitter Saturation Voltage	-	-	0.40	V	$I_{\rm C}$ = 0.4 mA, $E_{\rm E}$ = 1.7 mW/cm <sup>2</sup>

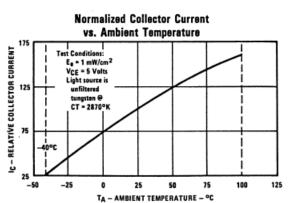
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## OP593, OP598 Series



**Typical Spectral Response** 100 100 OP598 (A) GaAlAs (B) GaAs Relative Response - % 80 (D) Tungsten 2870°K 10 OP593 IC(ON) – ON STATE COLLECTOR CURRENT – mA (C) GaAIAs 60 (D) GaAs (E) Tungsten 2870°K 1 40 20 0,1 0 600 700 800 900 1000 1100 Wavelength - nm 0.01





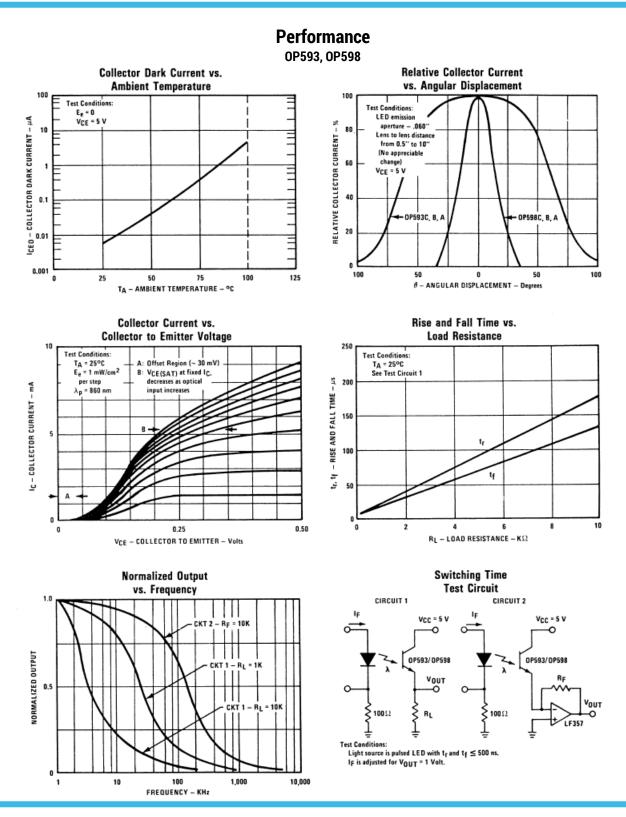
Performance

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